

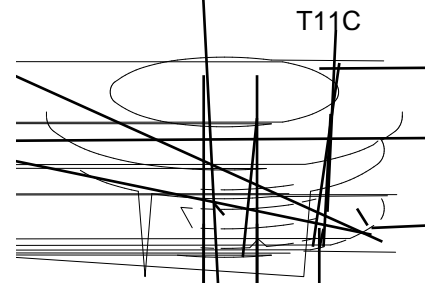
# KK2000-FAST SWITCHING THYRISTOR

1800-2000 V<sub>DRM</sub>

## HIGH POWER THYRISTOR FOR INVERTER APPLICATION

### Features:

- . All Diffused Structure
- . Amplifying Gate Configuration
- . Blocking capability up to 2000 volts
- . High dv/dt Capability
- . Pressure Assembled Device



## ELECTRICAL CHARACTERISTICS AND RATINGS

### Blocking - Off State

Device Type	V <sub>RRM</sub> (1)	V <sub>DRM</sub> (1)	V <sub>RSM</sub> (1)
KK2000/18	1800	1800	2000
KK2000/20	2000	2000	2100

V<sub>RRM</sub> = Repetitive peak reverse voltage  
V<sub>DRM</sub> = Repetitive peak off state voltage  
V<sub>RSM</sub> = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I <sub>RRM</sub> /I <sub>DRM</sub>	5 mA 80 mA (3)
Critical rate of voltage rise	dv/dt (4)	1000 V/μs

### Conducting - On State

# ELECTRICAL CHARACTERISTICS AND RATINGS KK2000-FAST SWITCHING THYRISTOR

## Gating

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Peak gate power dissipation	$P_{GM}$		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	$I_{GT}$		150		mA	$V_D=12V; R_L=3ohms; T_j=+25^{\circ}C$
Gate- trigger voltage	$V_{GT}$	0.70	2.5		V	$V_{tR}$

